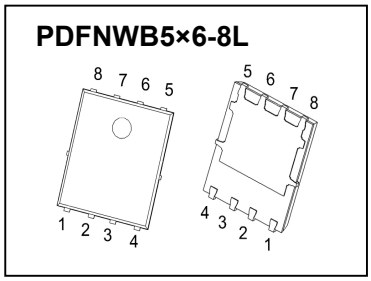
PDFNWB5×6-8L Plastic-Encapsulate MOSFETS

AC40SN10L N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$TYP	I_D
100V	13mΩ@10V	40A
	18mΩ@4.5V	



DESCRIPTION

The AC40SN10L uses shielded gate trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications

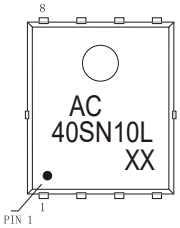
FEATURES

- High Power and current handing capability
- Load switch
- High density cell design for ultra low $R_{DS(ON)}$
- Lead free product is acquired
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

APPLICATIONS

- SMPS and general purpose applications
- Hard switched and high frequency circuits
- Uninterruptible Power Supply
- Power management

MARKING

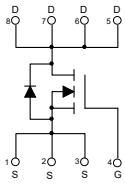


AC40SN10L = Part No.

Solid dot = Pin1 indicator.

XX = Code.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D ①	40	A
Pulsed Drain Current	I_{DM} ②	160	A
Single Pulsed Avalanche Energy	E_{AS} ③	96	mJ
Power Dissipation	P_D ①	104	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$ ⑥	62.5	℃/W
Thermal Resistance from Junction to Case	$R_{\theta JC}$ ①	1.2	℃/W
Operating Junction and Storage Temperature Range	T_J ,T_{stg}	-55~+150	℃

MOSFET ELECTRICAL CHARACTERISTICS

T_J=25℃ unless otherwise specified

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Off characteristics							
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250uA		100			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =80V, V_{GS} =0V	T_J =25℃			1.0	μA
			T_J =150℃			100	
Gate-body leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =±20V				±100	nA
On characteristics ④							
Gate-threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250uA		1.4	1.8	2.4	V
Static drain-source on-sate resistance	$R_{DS(on)}$	V_{GS} =10V, I_D =20A			13	16	mΩ
		V_{GS} =4.5V, I_D =10A			18	25	mΩ
Dynamic characteristics ⑤							
Input capacitance	C_{iss}	V_{DS} =50V,V_{GS} =0V, f =100KHz			1020		pF
Output capacitance	C_{oss}				177		
Reverse transfer capacitance	C_{rss}				5		
Gate resistance	R_g	f =1MHz			3		Ω
Switching characteristics ⑤							
Total gate charge	Q_g	V_{GS}=4.5V,V_{DS}=50V,I_D=20A			11.1		nC
Total gate charge	Q_g	V_{GS}=10V, V_{DS}=50V, I_D=20A			20.4		
Gate-source charge	Q_{gs}				1.9		
Gate-drain charge	Q_{gd}				4.4		
Turn-on delay time	$t_{d(on)}$	V_{DS}=50V,I_D=14A, V_{GS}=10V,R_G=10Ω			20		ns
Turn-on rise time	t_r				18		
Turn-off delay time	$t_{d(off)}$				114		
Turn-off fall time	t_f				62		
Drain-Source Diode Characteristics							
Drain-source diode forward voltage	V_{SD} ④	V_{GS} =0V, I_S=20A				1.2	V
Continuous drain-source diode forward current	I_S ①					40	A
Pulsed drain-source diode forward current	I_{SM} ②					160	A

Notes:

1.T_C=25℃ Limited only by maximum temperature allowed.

2.P_W≤10μs, Duty cycle≤1%.

3.EAS condition: V_{DD}=50V,V_{GS}=10V, L=0.5mH, R_g=25Ω Starting T_J = 25℃.

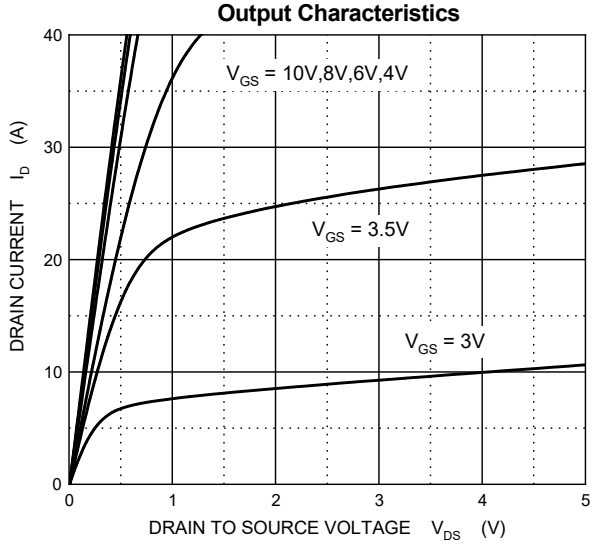
4.Pulse Test : Pulse Width≤300μs, duty cycle ≤2%.

5.Guaranteed by design, not subject to production.

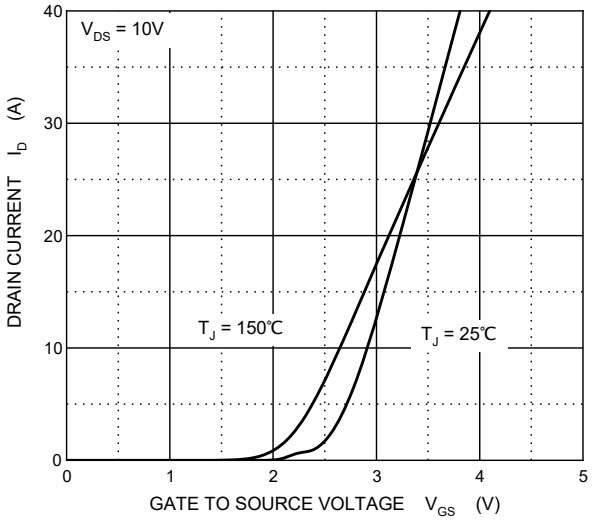
6.Device mounted on 1 in^2 FR-4 board with 2oz. single-sided Copper, in a still air environment with T_A=25 ℃.

Typical Characteristics (T_J = 25℃, unless otherwise specified)

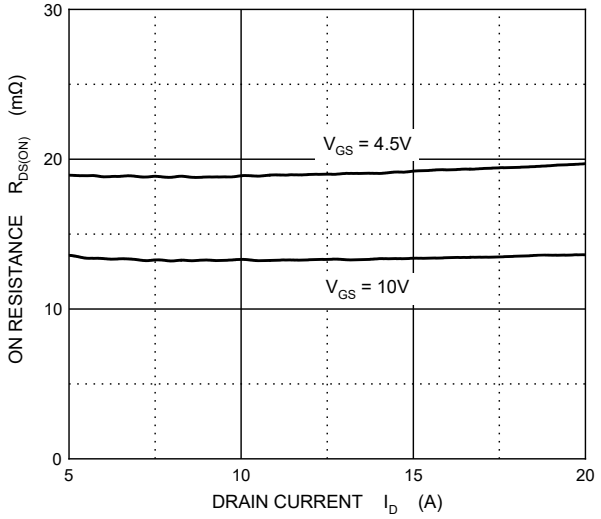
Output Characteristics



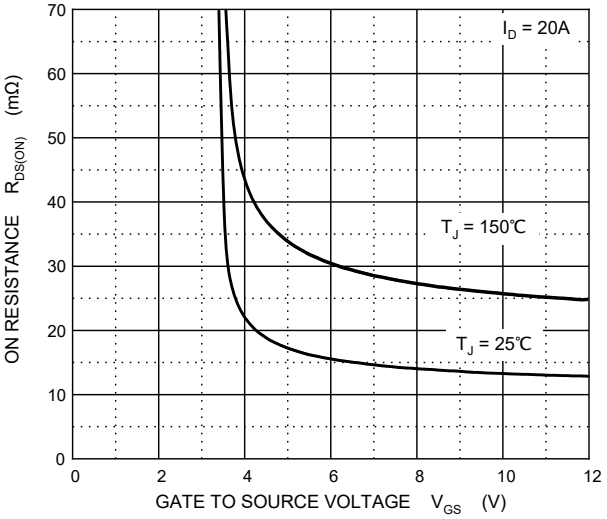
Transfer Characteristics



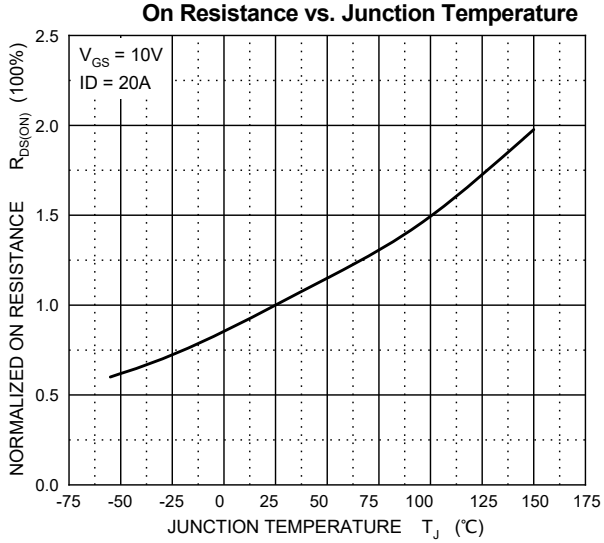
On Resistance vs. Drain Current



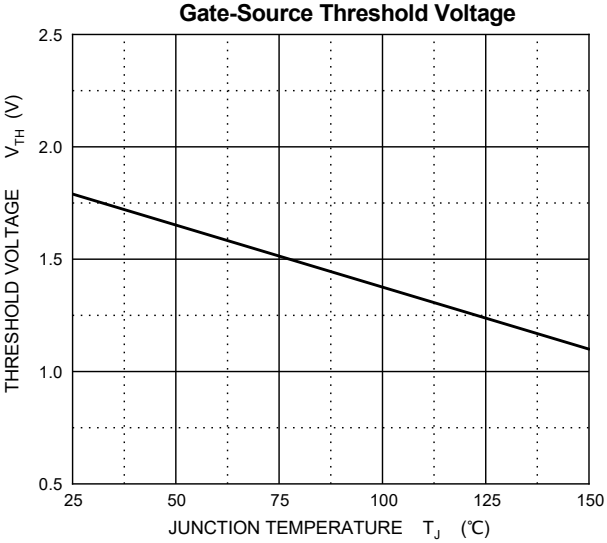
On Resistance vs. Gate-Source Bias



On Resistance vs. Junction Temperature

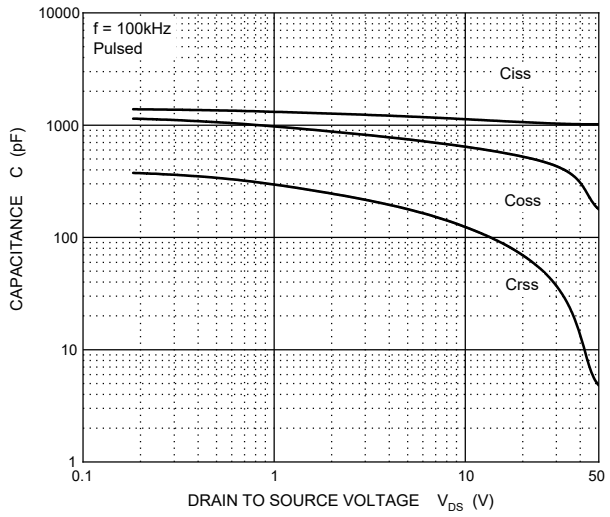


Gate-Source Threshold Voltage

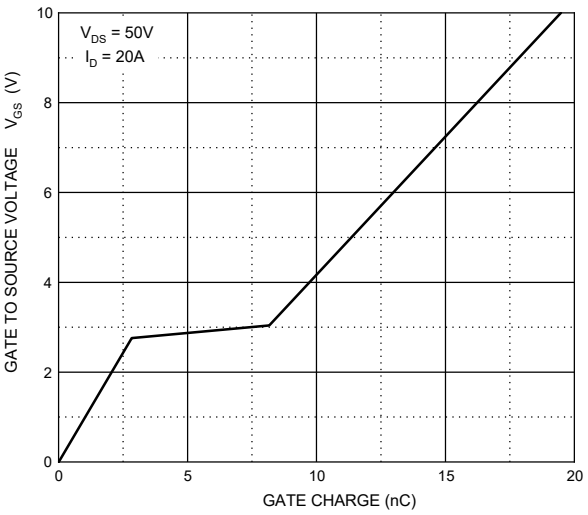


Typical Characteristics (T_J = 25℃, unless otherwise specified)

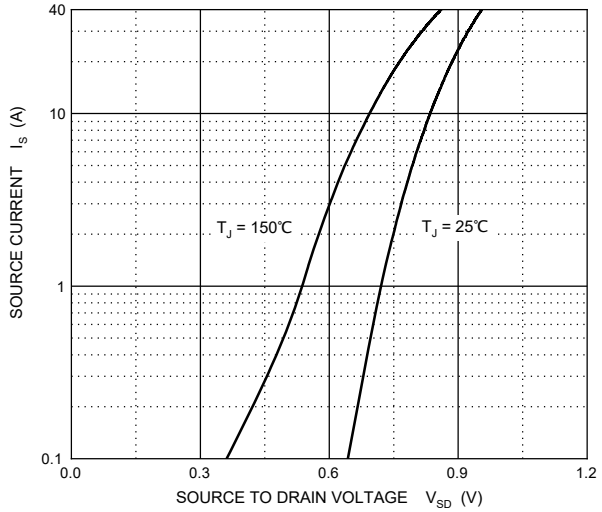
Typical Capacitances



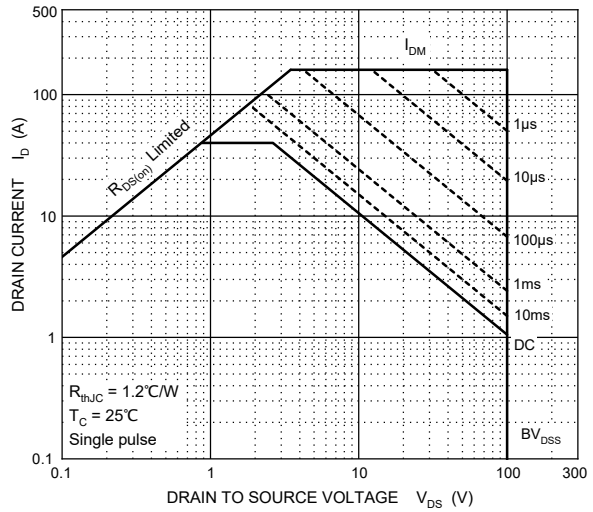
Gate Charge



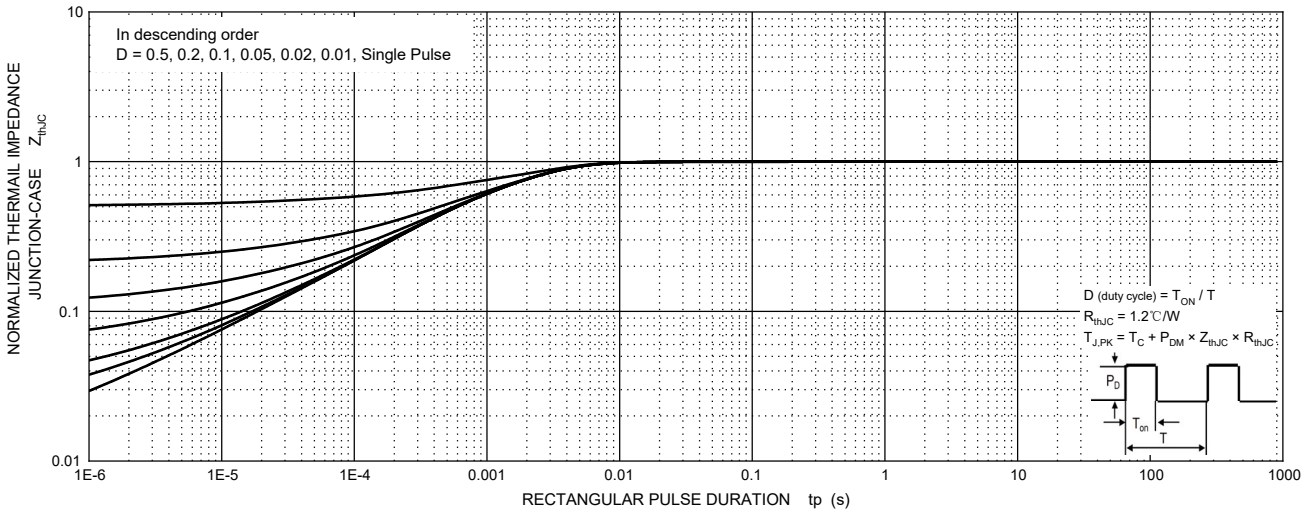
Source-Drain Diode Forward Characteristics



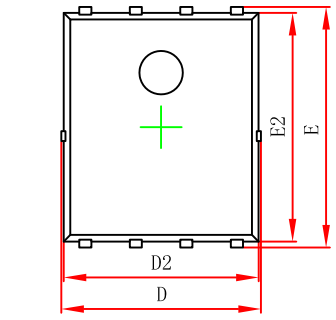
Maximum Safe Operating Area



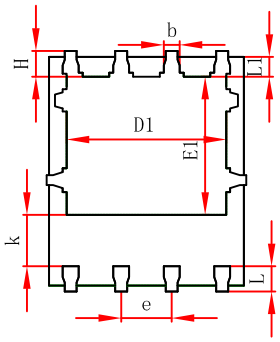
Transient Thermal Impedance, Junction-Case



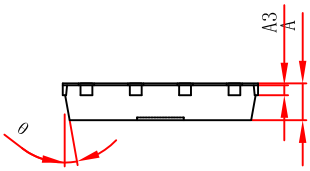
PDFNWB5x6-8L Package Outline Dimensions



Top View
[顶视图]



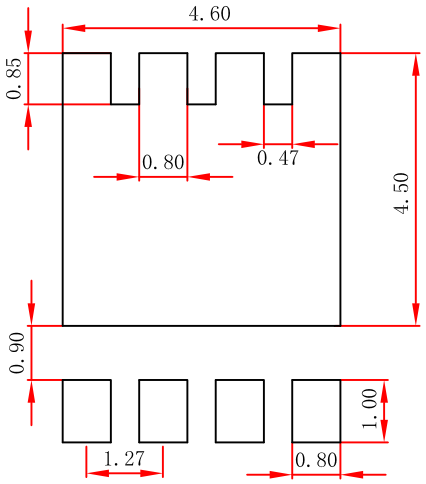
Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

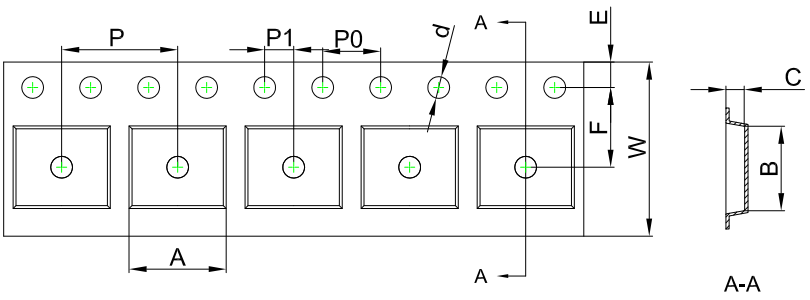
PDFNWB5x6-8L Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

PDFNWB5×6 Tape and Reel

PDFNWB5×6-8L Embossed Carrier Tape

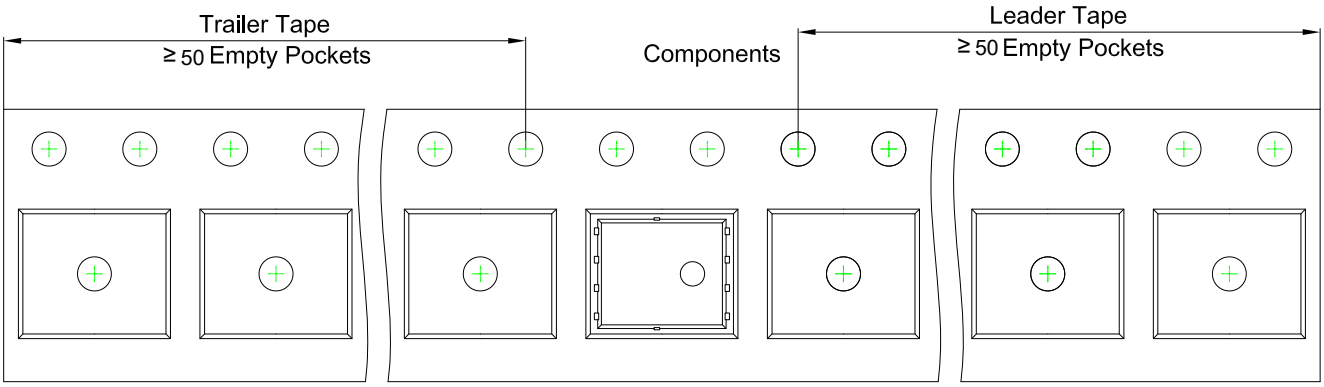


Packaging Description:

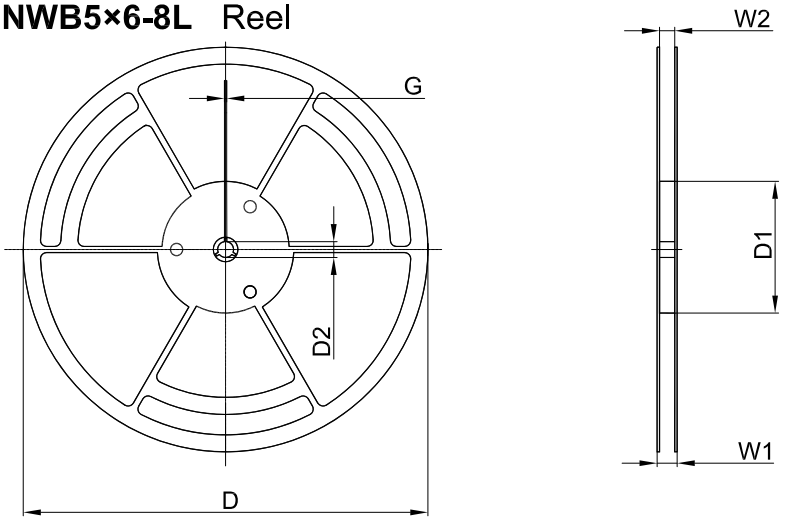
PDFNWB5×6-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 5,000 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
PDFNWB5×6-8L	6.30	5.30	1.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFNWB5×6-8L Tape Leader and Trailer



PDFNWB5×6-8L Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	G	W1	W2
13"Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	5,000 pcs	340×336×29	50,000 pcs	353×346×365